






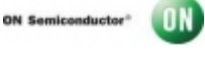


 	<h2 style="color: red;">HGT1S2N120CN</h2> <p>Hersteller-Teilenummer: HGT1S2N120CN</p> <p>Hersteller / Marke: Fairchild/ON Semiconductor</p> <p>Teil der Beschreibung: IGBT 1200V 13A 104W I2PAK</p> <p>Datenblätter:  HGT1S2N120CN.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 21000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
 <p>Not Actual Photo YIC International Co., Limited.</p>	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	HGT1S2N120CN
Hersteller	Fairchild/ON Semiconductor
Beschreibung	IGBT 1200V 13A 104W I2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-IGBTs
Teilstatus	21000 pcs Stock
Serie	-
Eingabetyp	Standard
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Through Hole
Leistung - max	104W
Verpackung / Gehäuse	TO-262-3 Long Leads, IPak, TO-262AA
Supplier Device-Gehäuse	TO-262
Strom - Kollektor (Ic) (max)	13A
Spannung - Kollektor-Emitter-Durchbruch (max)	1200V
IGBT-Typ	NPT
VCE (on) (Max) @ Vge, Ic	2.4V @ 15V, 2.6A
Strom - Collector Pulsed (Icm)	20A
Schaltenergie	96µJ (on), 355µJ (off)
Gate-Ladung	30nC
Td (ein / aus) bei 25 ° C	25ns/205ns
Testbedingung	960V, 2.6A, 51 Ohm, 15V
Verpackung	Tube













































HGT1S2N120CN ist neu im Original, Suche HGT1S2N120CN Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie HGT1S2N120CN Fairchild/ON Semiconductor mit Garantie und Vertrauen. Anfrage HGT1S2N120CN: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>HGT1S3N60A4DS9A AMI Semiconductor / ON Semiconductor IGBT 600V 17A 70W D2PAK</p>	 <p>HGT1S3N60A4DS FAIRCHILD HGT1S3N60A4DS FAIRCHILD</p>	 <p>HGT1S20N60C3S FSC FSC TO-263</p>	 <p>HGT1S3N60C3DS9A INTERSIL HGT1S3N60C3DS9A INTERSIL</p>
 <p>HGT1S3N60B3DS INTERSIL HGT1S3N60B3DS INTERSIL</p>	 <p>HGT1S2N120CN AMI Semiconductor / ON Semiconductor IGBT 1200V 13A 104W I2PAK</p>	 <p>HGT1S20N60C3RS FAIRCHILD HGT1S20N60C3RS FAIRCHILD</p>	 <p>HGT1S3N60A4DS9A Fairchild/ON Semiconductor IGBT 600V 17A 70W D2PAK</p>

heiße Teile

Mehr

 HGT1N30N60A4	 HGT1N40N60A4	 HGT1S10N120BNS	D HGT1S10N120BNS	 HGT1S10N120BNST
 HGT1S10N120BNST	 HGT1S12N60C3	D HGT1S12N60C3DS	 HGT1S12N60C3DS9A	 HGT1S12N60C3S
 HGT1S14N40G3VLS	 HGT1S14N41G3VL29A	 HGT1S14N41G3VLS9A	 HGT1S15N120C3ST	 HGT1S1N120CNDST
D HGT1S20N36G3VLS	 HGT1S20N36G3VLSR4737	 HGT1S20N60A4S9A	 HGT1S20N60A4S9A	 HGT1S20N60C3R
 HGT1S20N60C3RS	 HGT1S2N120CN	 HGT1S3N60A4DS	 HGT1S3N60A4DS9A	 HGT1S3N60A4DS9A
 HGT1S3N60B3DS	 HGT1S3N60C3DS9A	D HGT1S7N60A4DS	 HGT1S7N60A4DS	 HGT1S7N60A4DS.G7N60A4D
 HGT1S7N60A4DS9A	D HGT1S7N60A4S9A	 HGT1S7N60B3	 HGT1S7N60B3DS	 HGT1S7N60B3S
 HGT1S7N60C3DS9A	 HGT1S7N60C3DS9A	 HGTD1N120BNS9A	 HGTD1N120BNS9A	 HGTG10N120BND
 HGTG10N120BND	 HGTG11N120CN	 HGTG11N120CN	D HGTG11N120CND	 HGTG11N120CND
 HGTG12N60A4	 HGTG12N60A4	 HGTG12N60A4D	 HGTG12N60A4D	 HGTG12N60B3D

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